



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Judy Huang

Serial No.: Unknown

Filed: Herewith

For: Plasma Treatment To Enhance
Adhesion And To Minimize
Oxidation Of Carbon-Containing
Layers

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Group Art Unit: Unknown

Examiner: Unknown

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Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir: **BEST AVAILABLE COPY**

CERTIFICATE OF MAILING	
37 C.F.R. 1.10	
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<u>6/18/99</u> Date	<u>Beeth Mulachy</u> Signature

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The applicant, and the attorney who signs below on the basis of the information supplied by the inventor and the information in his file, submit herewith patents, publications, or other information of which they are aware, which may be material to the examination of this application and in respect of which there may be a duty to disclose in accordance with 37 C.F.R. 1.56.

While the information submitted in this Information Disclosure Statement may be "material" pursuant to 37 C.F.R. 1.56, it is not intended to constitute an admission that any patent, publication, or other information referred to therein is "prior art" for this invention unless specifically designated as such.

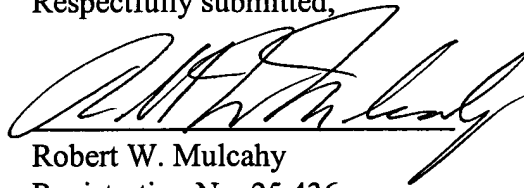
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The patents and/or publications submitted herewith are set forth on the attached Form PTO-1449.

In the event a fee is required in connection with the enclosed Information Disclosure Statement, the Commissioner of Patents and Trademarks is authorized to charge Deposit Account No. 01-1651/AMAT/3577/PDD/KPU1/JW for the necessary amount.

Respectfully submitted,

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U.S. Department of Commerce, Patent and Trademark Office					Docket No.		Serial No.	
					AMAT/3577/PDD/KPU1/JW		Unknown	
LIST OF REFERENCES CITED BY APPLICANT					Applicant			
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					Filing Date		Group	
					Herewith		Unknown	
U.S. Patent Documents								
*Examiner Initial		Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate	
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Translation								
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	AM	K. Mikagi, H. Ishikawa, T. Usami, M. Suzuki, K. Inoue, N. Oda, S. Chikaki, I. Sakai and T. Kikkawa, "Barrier Metal Free Copper Damascene Interconnection Technology Using Atmospheric Copper Reflow and Nitrogen Doping in SiOF Film," © 1996 IEEE, IEDM 96 365-368, Pages 14.5.1-14.5.4						
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	AO	Takahi Ito, Takao Nozaki, and Hajime Ishikawa, "Direct Thermal Nitridation of Silicon Dioxide Films in Anhydrous Ammonia Gas," Optical Properties, Vol. 127, No. 9, September, 1980, Pages 2053-2057						
Examiner			Date Considered					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

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U.S. Patent Documents								
*Examiner Initial		Document Number	Issue Date	Name	Class	Subclass	Filing Date If Appropriate	
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	BI							
Foreign Patent Documents								
							Translation	
		Document Number	Date	Country	Class	Subclass	Yes	No
	BL							
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	BM	Richard Swope, Woo Sik Yoo, Julian Hsieh, Shari Shuchmann, Ferenc Nagy, Harald te Nijenhuis, and David Mordo, "Improvement of Adhesion Properties of Fluorinated Silica Glass Films by Nitrous Oxide Plasma Treatment," J. Electrochem. Soc., Vol. 144, No. 7, July, 1997 © The Electrochemical Society, Inc., Pages 2559-2564						
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